

### KTA2015 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.1 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$ : -35 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-35V, I_E=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-6V, I_C=-400mA$	O Y	25 40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-100mA$			-1	V
Transition frequency	$f_T$	$V_{CE}=-6V, I_C=-20mA$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-6V, I_E=0, f=1MHz$		13		pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	ZO	ZY